

**•General Description**

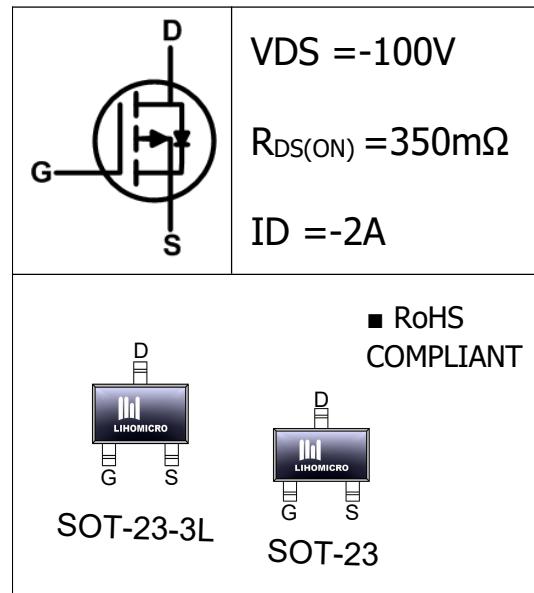
The LH02P10 uses trench technology and design to provide excellent  $R_{DS(on)}$  with low gate charge. This device is suitable for high current load applications.

**•Features**

- Advance high cell density Trench technology
- Low RDS(ON) to minimize conductive loss
- Low Gate Charge for fast switching

**•Application**

- LED/LCD/PDP TV and monitor Lighting
- Power Supplies


**•Ordering Information:**

Part Number	LH02P10	LH02P10
Package	SOT-23	SOT-23-3L
Basic Ordering Unit (pcs)	3000	3000
Normal Package Material Ordering Code	LH02P10S23-SOT23-TAP	LH02P10S23L-SOT23-TAP
Halogen Free Ordering Code	LH02P10S23-SOT23-TAP-HF	LH02P10S23L-SOT23-TAP-HF

**•Absolute Maximum Ratings (TC = 25°C)**

PARAMETER	SYMBOL	Value	UNIT
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-100	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub> (T <sub>A</sub> = 25°C)	-2	A
	I <sub>D</sub> (T <sub>A</sub> = 70°C)	-1.8	A
Pulsed drain current (T <sub>A</sub> = 25°C, tp limited by T <sub>jmax</sub> ) <sup>1</sup>	I <sub>DM</sub>	-5	A
Power Dissipation(TC=25°C)	P <sub>D</sub> (T <sub>A</sub> =25°C)	1	W
	P <sub>D</sub> (T <sub>A</sub> =70°C)	0.8	W
Operating Temperature	T <sub>J</sub>	-50~+150	°C
Storage Temperature	T <sub>STG</sub>	-50~+150	°C

**• Electronic Characteristics**

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	-100	--	--	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	-1.0	-1.5	-2.5	V
Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -1A$	--	350	520	$m\Omega$
		$V_{GS} = -4.5V, I_D = -1A$	--	400	560	
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = -80V, V_{GS} = 0V, T_J = 25^\circ C$	--	--	10	$\mu A$
		$V_{DS} = -80V, V_{GS} = 0V, T_J = 125^\circ C$	--	--	100	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	--	--	$\pm 100$	nA

**Dynamic Electrical Characteristics @  $T_J = 25^\circ C$  (Unless otherwise stated)**

Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = -15V, f = 1.0MHz$	--	553	--	pF
Output Capacitance	$C_{oss}$		--	29	--	
Reverse transfer Capacitance	$C_{rss}$		--	20	--	
Total Gate Charge	$Q_g$	$V_{DS} = -15V, I_D = -0.5A, V_{GS} = -4.5V$	--	4.5	--	nC
Gate Source Charge	$Q_{gs}$		--	1.1	--	
Gate Drain Charge	$Q_{gd}$		--	1.6	--	

**Switching Characteristics**

Turn-on Delay Time	$T_{d(on)}$	$V_{DD} = -50V, I_D = -0.5A, V_{GS} = -10V, R_G = 3.3\Omega$	--	13.5	--	nS
Turn-on Rise Time	$T_r$		--	6.8	--	
Turn-Off Delay Time	$T_{d(off)}$		--	34	--	
Turn-Off Fall Time	$T_f$		--	3	--	

**Source Drain Diode Characteristics**

Continuous Source Current	$I_s$	$V_G = V_D = 0V$ , Force Current	--	--	1.8	A
Diode Forward Voltage	$V_{SD}$	$T_J = 25^\circ C, I_s = -1.0A, V_{GS} = 0V$	--	-0.84	-1.2	V

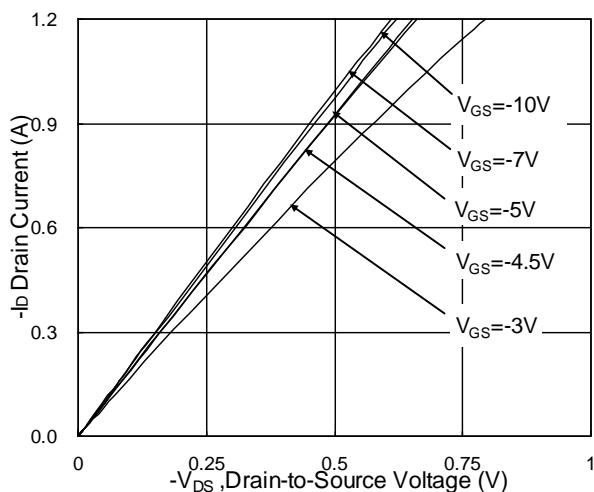
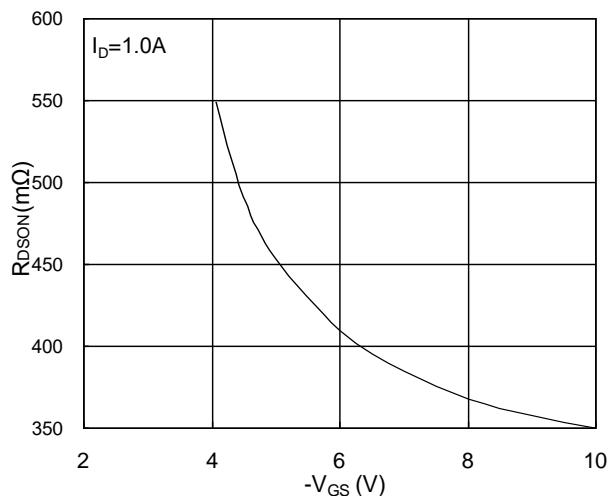
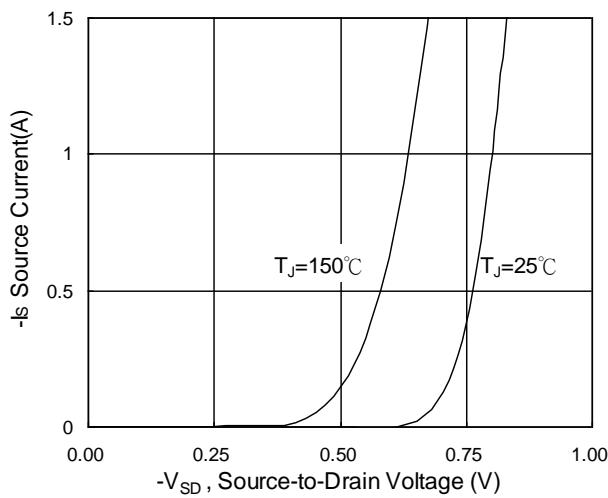
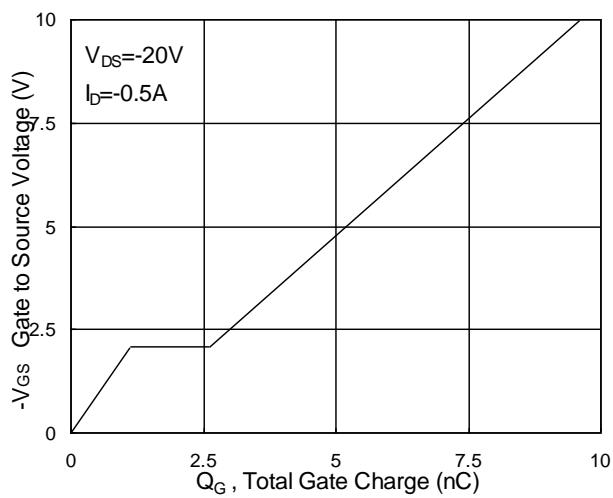
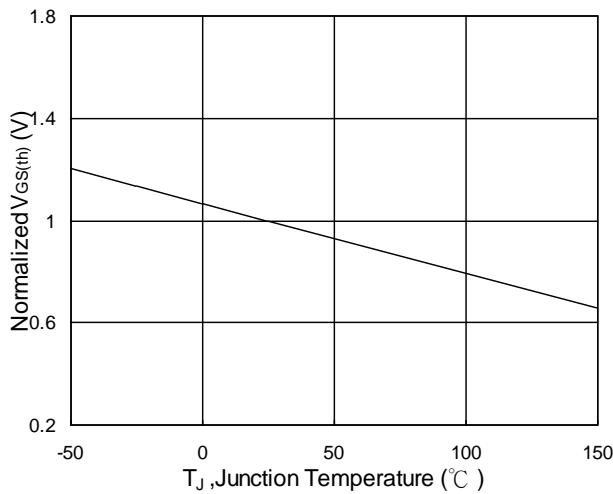
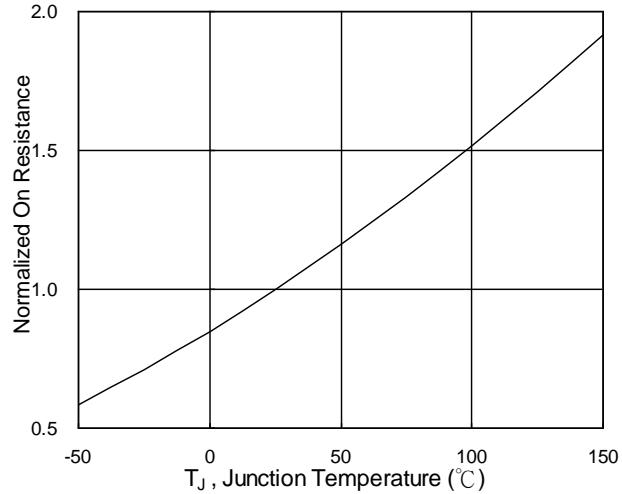
**• Thermal Characteristics**

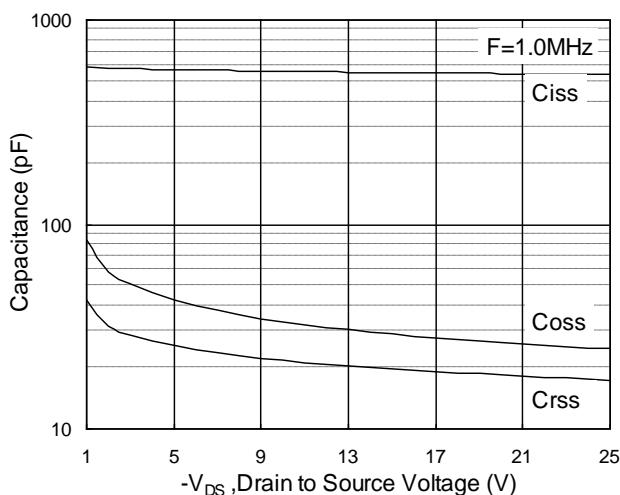
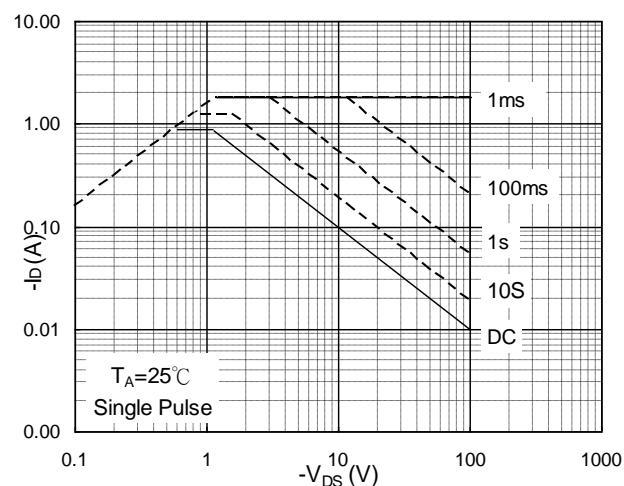
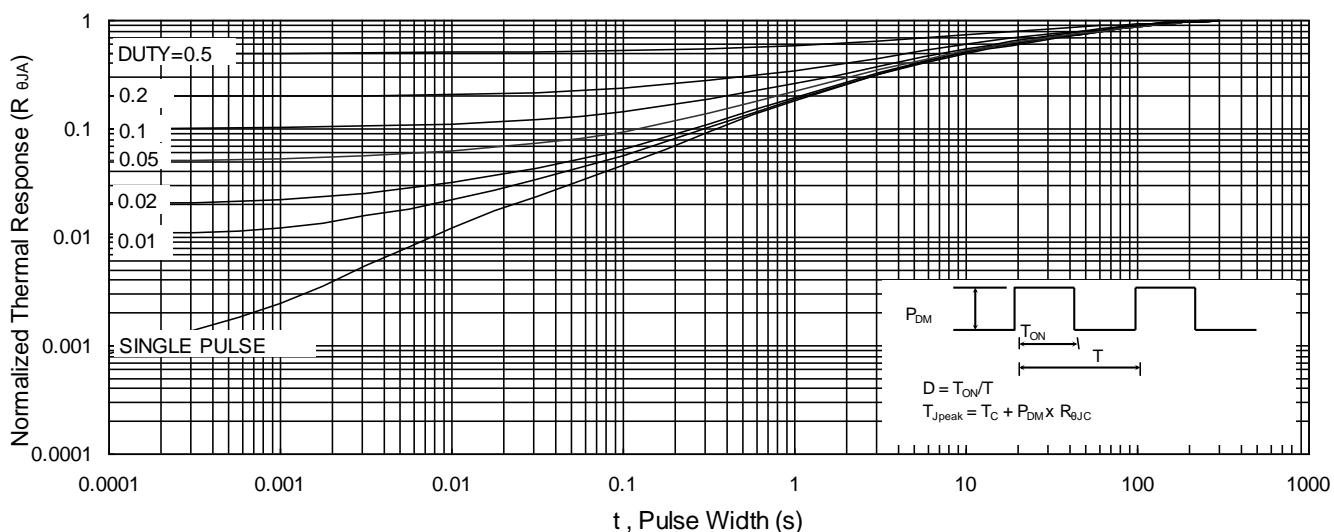
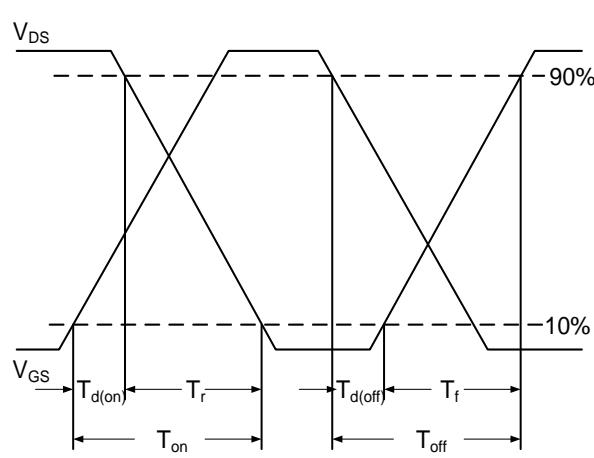
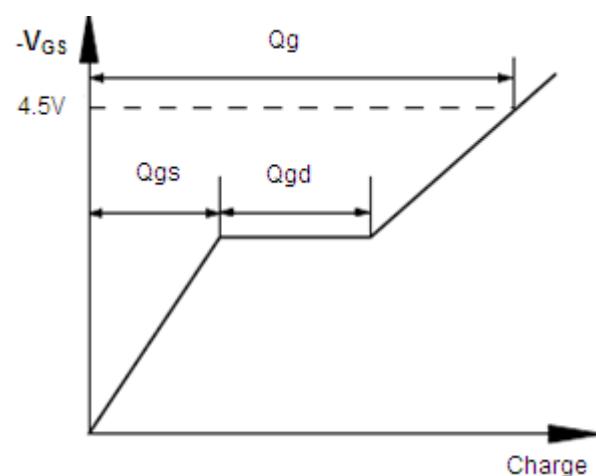
PARAMETER	SYMBOL	MAX		UNIT
Maximum Junction-ambient	$R_{thJA}$	125		$^\circ C/W$

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

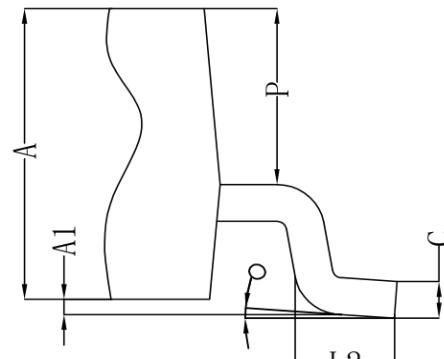
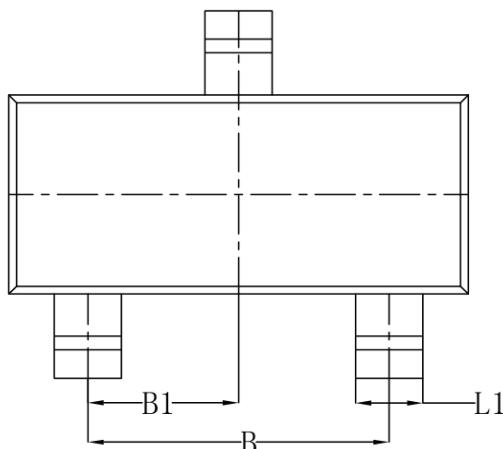
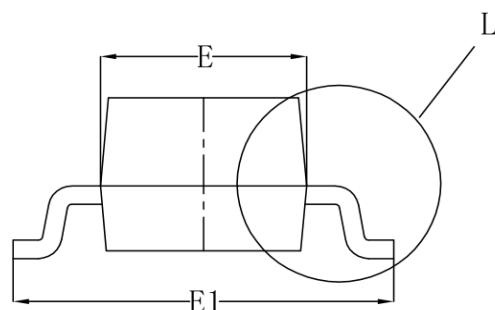
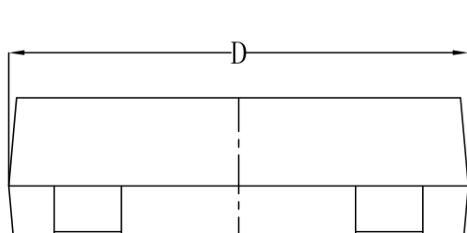
 2. Pulse Test : Pulse width  $\leq 300 \mu s$ , Duty cycle  $\leq 2\%$ .

**•Typical Characteristics**

**Fig.1 Typical Output Characteristics**

**Fig.2 On-Resistance vs. Gate-Source**

**Fig.3 Forward Characteristics Of Reverse**

**Fig.4 Gate-Charge Characteristics**

**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$** 

**Fig.6 Normalized  $R_{DSON}$  vs.  $T_J$**

**•Typical Characteristics(cont.)**

**Fig.7 Capacitance**

**Fig.8 Safe Operating Area**

**Fig.9 Normalized Maximum Transient Thermal Impedance**

**Fig.10 Switching Time Waveform**

**Fig.11 Gate Charge Waveform**

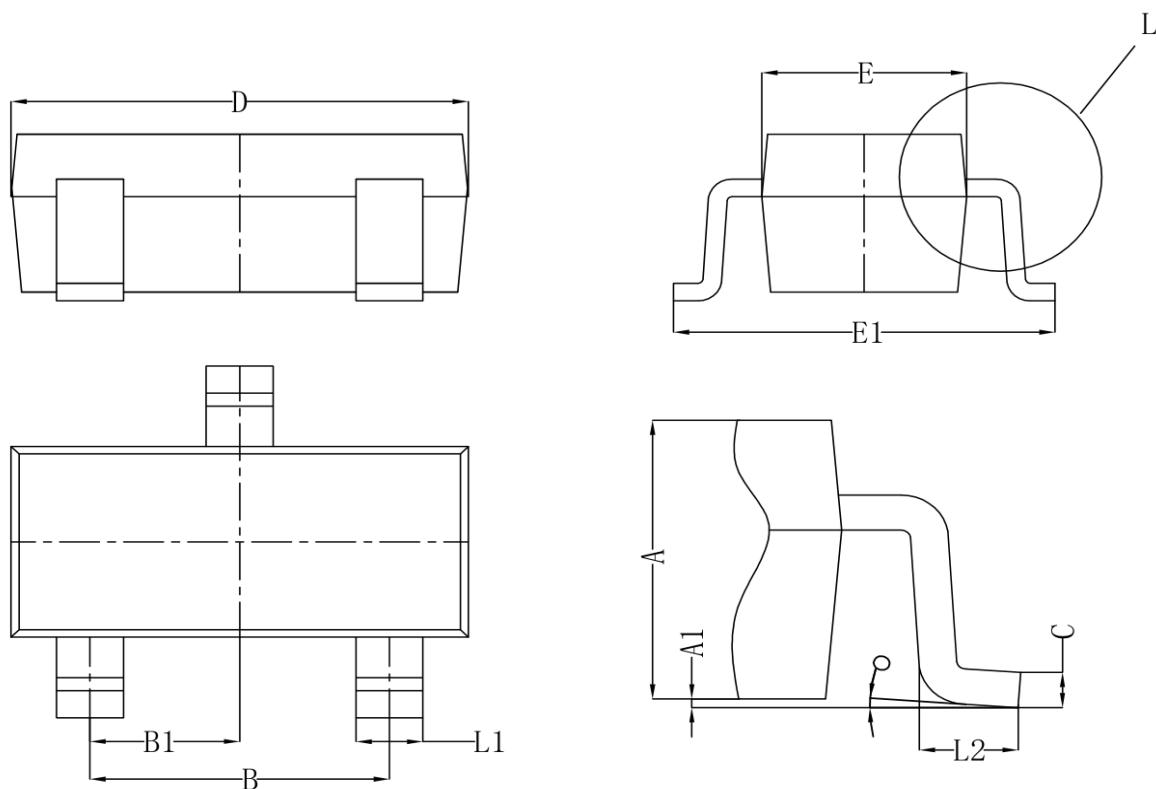
**•Dimensions(SOT-23)**

Symbol	Dim in mm		
	Min	Nor	Max
A	0.900	1.000	1.100
A1	0.000	0.050	0.100
L1	0.350	0.400	0.500
C	0.100	0.110	0.120
D	2.800	2.900	3.000
E	1.250	1.300	1.350
E1	2.250	2.400	2.550
B	1.800	1.900	2.000
B1	0.950 TYP		
L2	0.200	0.350	0.450
P	0.550	0.575	0.600


**Detial L**

**•Dimensions(SOT-23-3L)**

Symbol	Dim in mm		
	Min	Nor	Max
A	1.050	1.100	1.150
A1	0.000	0.050	0.100
L1	0.300	0.400	0.500
C	0.100	0.150	0.200
D	2.820	2.920	3.020
E	1.500	1.600	1.700
E1	2.650	2.800	2.950
B	1.800	1.900	2.000
B1	0.950 TYP		
L2	0.300	0.450	0.600
O	0°	4°	8°


**Detail L**